



Low On-Resistance Wideband/Video Switches

DESCRIPTION

The DG641, DG642, DG643 are high performance monolithic video switches designed for switching wide bandwidth analog and digital signals. DG641 is a quad SPST, DG642 is a single SPDT, and DG643 is a dual SPDT function. These devices have exceptionally low on-resistances (5 Ω typ-DG642), low capacitance and high current handling capability.

To achieve TTL compatibility, low channel capacitances and fast switching times, the DG641, DG642, DG643 are built on the Vishay Siliconix proprietary D/CMOS process. Each switch conducts equally well in both directions when on, and blocks up to 14 $\rm V_{p-p}$ when off. An epitaxial layer prevents latchup.

FEATURES

- Wide bandwidth: 500 MHz
 Low crosstalk at 5 MHz: 85 dB
- Low R_{DS(on)}: 5 Ω, DG642
- TTL logic compatible
- Fast switching: t_{ON} 50 ns
- · Single supply compatibility
- High current: 100 mA, DG642

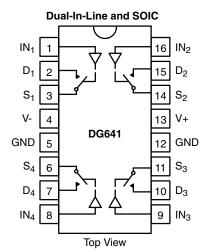
BENEFITS

- · High precision
- · Improved frequency response
- · Low insertion loss
- Improved system performance
- · Reduced board space
- Low power consumption

APPLICATIONS

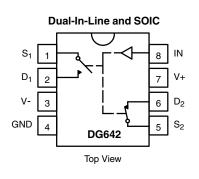
- · RF and video switching
- RGB switching
- · Video routing
- Cellular communications
- ATE
- Radar/FLIR systems
- Satellite receivers
- · Programmable filters

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE (DG641)				
Logic Switch				
0	OFF			
1	ON			

Logic "0" \leq 0.8 V Logic "1" \geq 2.4 V



TRUTH TABLE (DG642)							
Logic	Logic SW ₁ SW ₂						
0	OFF	ON					
1	ON	OFF					

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

	Dual-In-Line and SOIC				
		,			
IN ₁	16	IN ₂			
D_1	2 15	D ₂			
GND	3 7 14	GND			
S ₁	4 13	S ₂			
V-	5 12	V+			
S_4	6 11	S_3			
GND	7 1 10	GND			
D ₄	B DG643 9	D ₃			
	Top View				

TRUTH TABLE (DG643)						
Logic SW ₁ , SW ₂ SW ₃ , SW ₄						
0	ON					
1	ON	OFF				

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V



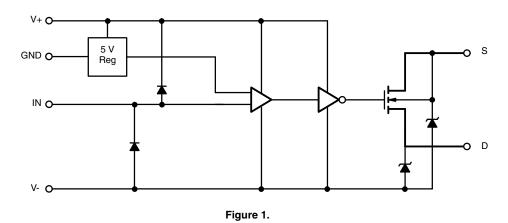
ORDERING INFORMATION						
Temp. Range	Package	Part Number				
DG641						
- 40 °C to 85 °C	16-Pin Plastic DIP	DG641DJ				
	16-Pin Narrow SOIC	DG641DY				
DG642						
40.00 105.00	8-Pin Plastic DIP	DG642DJ				
- 40 °C to 85 °C	8-Pin Narrow SOIC	DG642DY				
DG643						
- 40 °C to 85 °C	16-Pin Plastic DIP	DG643DJ				
- 40 C to 85 C	16-Pin Narrow SOIC	DG643DY				

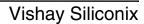
Parameter		Symbol Limit		Unit
V+ to V-			- 0.3 to 21	
V+ to GND			- 0.3 to 21	
V- to GND			- 19 to + 0.3	
Digital Inputs			(V-) - 0.3 V to (V+) + 0.3 V or 20 mA, whichever occurs first	V
V_S, V_D			(V-) - 0.3 V to (V+) + 14 V or 20 mA, whichever occurs first	
Continuous Current (Any terminal except	t S or D)		20	
Continuous Current S or D	DG641, DG643		75	
Continuous Current 3 of D	DG642		100	mA
Current, S or D	DG641, DG643		200	
(Pulsed at 1 ms, 10 % duty cycle max)	DG642		300	
Storage Temperature			- 65 to 125	°C
	8-Pin Plastic DIP and Narrow SOIC ^c		300	
Power Dissipation (Package) ^b	16-Pin Plastic DIP ^d		470	mW
	16-Pin Narrow SOIC ^e		600	

Notes:

- $a. \ Signals \ on \ S_X, \ D_X, \ or \ IN_X \ exceeding \ V+ \ or \ V- \ will \ be \ clamped \ by \ internal \ diodes. \ Limit \ forward \ diode \ current \ to \ maximum \ current \ ratings.$
- b. All leads welded or soldered to PC board.
- c. Derate 7.6 mW/°C above 75 °C.
- d. Derate 6 mW/°C above 75 °C.
- e. Derate 80 mW/°C above 75 °C.

SCHEMATIC DIAGRAM (Typical Channel)







		Test Conditions Unless Otherwise Specified		- 4	Limits 10 °C to 85	°C	
Parameter	Symbol	$V_{INH} = 15 \text{ V}, V_{INL} = -3 \text{ V}$ $V_{INH} = 2.4 \text{ V}, V_{INL} = 0.8 \text{ V}^{e}$	Temp.a	Min.b	Typ. ^c	Max.b	Uni
Analog Switch							
Analog Signal Range ^d	V _{ANALOG}	V- = - 5 V, V+ = 12 V	Full	- 5		8	V
Analog dignal hange	VANALOG	V- = GND V, V+ = 12 V	Full	0		8	
Drain-Source On-Resistance	R _{DS(on)}	I _S = - 10 mA, V _D = 0 V	Room Full		8	15 20	Ω
R _{DS(on)} Match	$\Delta R_{DS(on)}$		Room		1	2	1
Source Off Leakage Current	I _{S(off)}	V _S = 0 V, V _D = 10 V	Room Full	- 10 - 100	- 0.02	10 100	
Drain Off Leakage Current	I _{D(off)}	V _S = 10 V, V _D = 0 V	Room Full	- 10 - 100	- 0.02	10 100	n <i>A</i>
Channel On Leakage Current	I _{D(on)}	$V_S = V_D = 0 V$	Room Full	- 10 - 100	- 0.1	10 100	
Digital Control							
Input Voltage High	V _{INH}		Full	2.4			٧
Input Voltage Low	V_{INL}		Full			0.8	
Input Current	I _{IN}	V _{IN} = GND or V+	Room Full	- 1 - 20	0.05	1 20	μA
Dynamic Characteristics							
On State Input Capacitance ^d	C _{S(on)}	$V_S = V_D = 0 V$	Room		10	20	
Off State Output Capacitance ^d	C _{S(off)}	V _S = 0 V	Room		4	12	pl
Off State Input Capacitance ^d	C _{D(off)}	V _D = 0 V	Room		4	12	
Bandwidth	BW	$R_L = 50 \Omega$, see figure 6	Room		500		MH
Turn On Time	t _{ON}	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}$	Room Full		50	70 140	ns
Turn Off Time	t _{OFF}	see figure 2	Room Full		28	50 85	
Charge Injection	Q	$C_L = 1000 \text{ pF}, V_D = 0 \text{ V}$ see figure 3	Room		- 19		рС
Off Isolation	OIRR	R_{IN} = 75 Ω , R_{L} = 75 Ω f = 5 MHz, see figure 4	Room		- 60		dE
All Hostie Crosstalk	X _{TALK}	$R_{IN} = 10 \Omega$, $R_{L} = 75 \Omega$ f = 5 MHz, see figure 5	Room		- 87		u L
Power Supplies							
Positive Supply Current	l+	V _{IN} = 0 V or V _{IN} = 5 V	Room Full		3.5	6 9	m/
Negative Supply Current	I-	IN - O V OI VIN - O V	Room Full	- 6 - 9	- 3		'''

Notes:

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating temperature suffix.
- b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- d. Guaranteed by design, not subject to production test.
- e. V_{IN} = input voltage to perform proper function.



		Test Conditions Unless Otherwise Specified V+ = 15 V, V- = - 3 V		- 4	Limits 10 °C to 85	°C	
Parameter	Symbol	$V_{INH} = 15 \text{ V}, V_{INL} = 0.8 \text{ V}^{e}$	Temp.a	Min.b	Typ. ^c	Max.b	Unit
Analog Switch							
Analog Signal Range ^d	V	V- = - 5 V, V+ = 12 V	Full	- 5		8	V
Analog digital Harige	V _{ANALOG}	V- = GND V, V+ = 12 V	Full	0		8	•
Drain-Source On-Resistance	R _{DS(on)}	I _S = - 10 mA, V _D = 0 V	Room Full		5	8 9	Ω
R _{DS(on)} Match	$\Delta R_{DS(on)}$	9	Room		0.5	1	1
Source Off Leakage Current	I _{S(off)}	V _S = 0 V, V _D = 10 V	Room Full	- 10 - 200	- 0.04	10 200	
Drain Off Leakage Current	I _{D(off)}	V _S = 10 V, V _D = 0 V	Room Full	- 10 - 200	- 0.04	10 200	nA
Channel On Leakage Current	I _{D(on)}	$V_S = V_D = 0 V$	Room Full	- 10 - 200	- 0.2	10 200	
Digital Control							
Input Voltage High	V _{INH}		Full	2.4			V
Input Voltage Low	V_{INL}		Full			0.8	ľ
Input Current	I _{IN}	V _{IN} = GND or V+	Room Full	- 1 - 20	0.05	1 20	μΑ
Dynamic Characteristics							
On State Input Capacitance ^d	C _{S(on)}	$V_S = V_D = 0 V$	Room		19	40	
Off State Input Capacitance ^d	C _{S(off)}	V _D = 0 V	Room		8	20	pF
Off State Output Capacitance ^d	C _{D(off)}	V _S = 0 V	Room		8	20	
Bandwidth	BW	$R_L = 50 \Omega$, see figure 6	Room		500		MH
Turn On Time	t _{ON}	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}$	Room Full		60	100 160	ns
Turn Off Time	t _{OFF}	see figure 2	Room Full		40	60 100	
Charge Injection	Q	$C_L = 1000 \text{ pF, } V_D = 0 \text{ V}$ see figure 3	Room		- 40		рC
Off Isolation		$R_{\text{IN}} = 75 \ \Omega, R_{\text{L}} = 75 \ \Omega$ f = 5 MHz, see figure 4	Room		- 63		- dB
All Hostie Crosstalk	X _{TALK(AH)}	R_{IN} = 10 Ω, R_L = 75 Ω f = 5 MHz, see figure 5	Room		- 85		4.0
Power Supplies							
Positive Supply Current	l+	V _{IN} = 0 V or V _{IN} = 5 V	Room Full		3.5	6 9	m.A
Negative Supply Current	I-	IN - O A OL AIN - O A	Room Full	- 6 - 9	- 3		'''

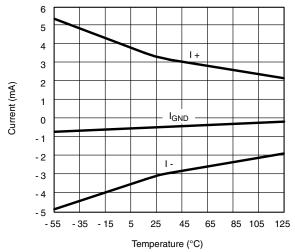
Notes:

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating temperature suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
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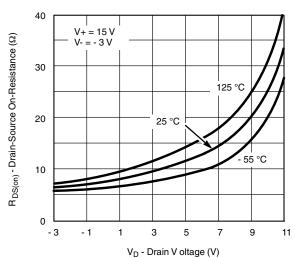
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



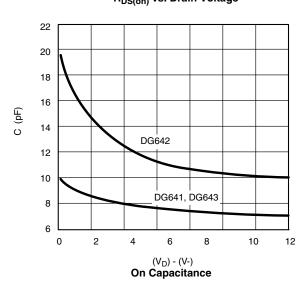
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

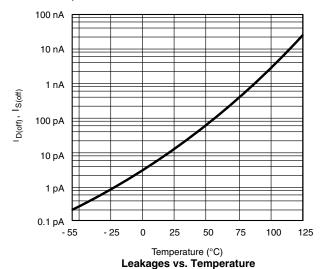


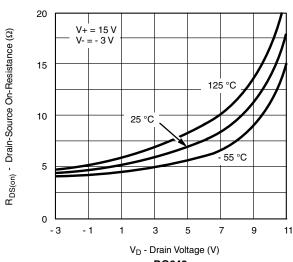
Supply Current vs. Temperature



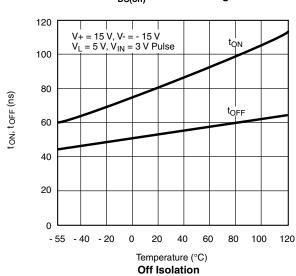
DG641, DG643 R_{DS(on)} vs. Drain Voltage





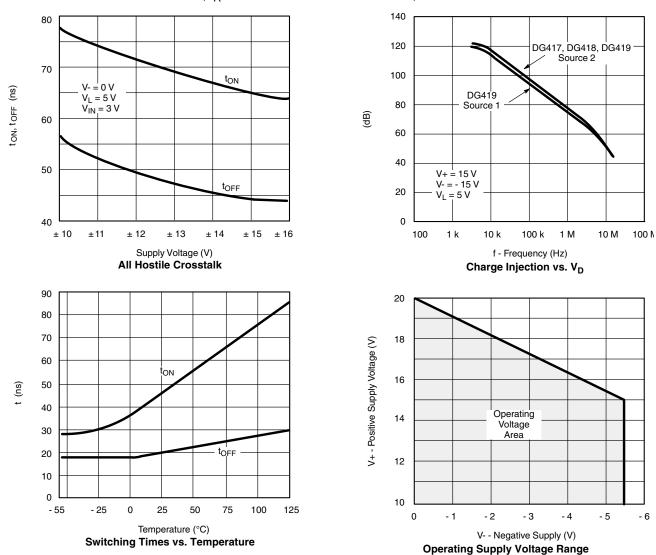


DG642 R_{DS(on)} vs. Drain Voltage





TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



TEST CIRCUITS

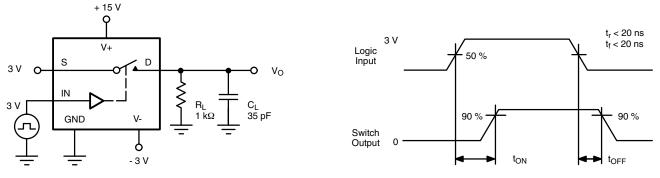
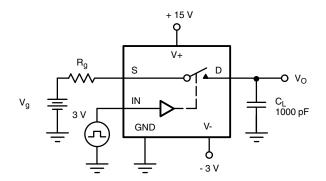
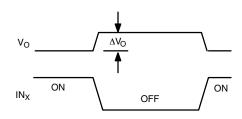


Figure 2. Switching Time



TEST CIRCUITS





 ΔV_O = measured voltage error due to charge injection The charge injection in coulombs is Q = C_L x ΔV_O

Figure 3. Charge Injection

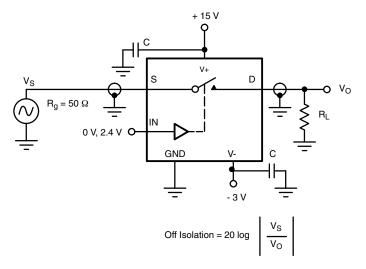


Figure 4. Off Isolation

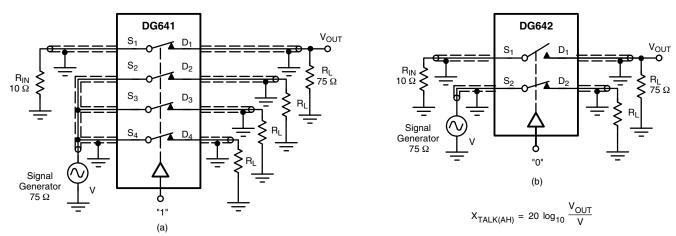


Figure 5. All Hostile Crosstalk - X_{TALK(AH)}

TEST CIRCUITS



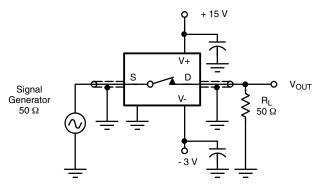


Figure 6. Bandwidth

APPLICATIONS

Device Description

The DG641, DG642, DG643 switches offer true bidirectional switching of high frequency analog or digital signals with minimum signal crosstalk, low insertion loss, and negligible non-linearity distortion and group delay.

Built on the Siliconix D/CMOS process, these switches provide excellent off-isolation with a bandwidth of around 500 MHz. The silicon-gate D/CMOS processing also yields fast switching speeds.

An on-chip regulator circuit maintains TTL input compatibility over the whole operating supply voltage range shown, easing control logic interfacing.

Circuit layout is facilitated by the interchangeability of source and drain terminals.

Frequency Response

A single switch on-channel exhibits both resistance $[R_{DS(on)}]$ and capacitance $[C_{S(on)}]$. This RC combination has an attenuation effect on the analog signal - which is frequency dependent (like an RC low-pass filter). The - 3 dB bandwidth of the DG641, DG642, DG643 is typically 500 MHz (into 50 Ω).

Power Supplies

Power supply flexibility is a useful feature of the DG641, DG642, DG643 series. It can be operated from a single positive supply (V+) if required (V- connected to ground). Note that the analog signal must not exceed V- by more than - 0.3 V to prevent forward biasing the substrate p-n junction. The use of a V- supply has a number of advantages:

1. It allows flexibility in analog signal handling, i.e., with $V-=-5\ V$ and $V+=12\ V$; up to $\pm\ 5\ V$ ac signals can be controlled.

- 2. The value of on capacitance $[C_{S(on)}]$ may be reduced. A property known as 'the body-effect' on the DMOS switch devices causes various parametric effects to occur. One of these effects is the reduction in $C_{S(on)}$ for an increasing V body-source. Note however that to increase V- normally requires V+ to be reduced (since V+ to V- = 21 V max.). A reduction in V+ causes an increase in $r_{DS(on)}$, hence a compromise has to be achieved. It is also useful to note that tests indicate that optimum video linearity performance (e.g., differential phase and gain) occurs when V- is around 3 V.
- V- eliminates the need to bias the analog signal using potential dividers and large coupling capacitors.

Decoupling

It is an established rf design practice to incorporate sufficient bypass capacitors in the circuit to decouple the power supplies to all active devices in the circuit. The dynamic performance of the DG641, DG642, DG643 series is adversely affected by poor decoupling of power supply pins. Also, of even more significance, since the substrate of the device is connected to the negative supply, adequate decoupling of this pin is essential. Suitable decoupling capacitors are 1- to 10 μF tantalum bead, plus 10- to 100-nF ceramic or polyester.

Rules:

- Decoupling capacitors should be incorporated on all power supply pins (V+, V-). (see figure 7).
- 2. They should be mounted as close as possible to the device pins.
- Capacitors should be of a suitable type with good high frequency characteristics - tantalum bead and/or ceramic disc types are adequate.



APPLICATIONS

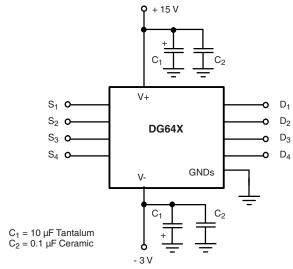


Figure 7. Supply Decoupling

Board Layout

PCB layout rules for good high frequency performance must also be observed to achieve the performance boasted by these analog switches. Some tips for minimizing stray effects are:

- Use extensive ground planes on double sided PCB, separating adjacent signal paths. Multilayer PCB is even better.
- 2. Keep signal paths as short as practically possible, with all channel paths of near equal length.
- Careful arrangement of ground connections is also very important. Star connected system grounds eliminate signal current, flowing through ground path parasitic resistance, from coupling between channels.

Figure 8 shows a 4-channel video multiplexer using a DG641.

In Figure 9, two coax cables terminated on 75 Ω bring two video signals to the DG642 switch. The two drains tied together lower the on-state capacitance. An Si582 video amplifier drives a double terminated 75 Ω cable. The double terminated coax cable eliminates line reflections.

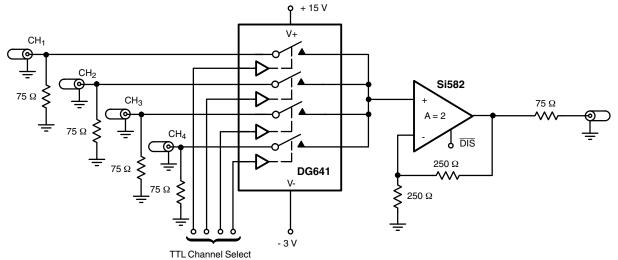


Figure 8. 4 by 1 Video Multiplexing Using the DG641

VISHAY.

APPLICATIONS

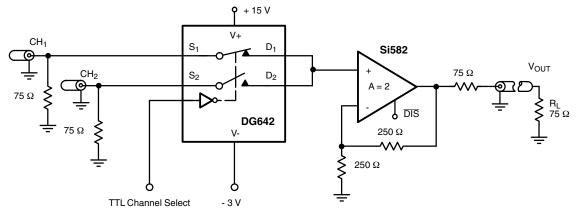


Figure 9. 2-Channel Video Selector Using the DG642

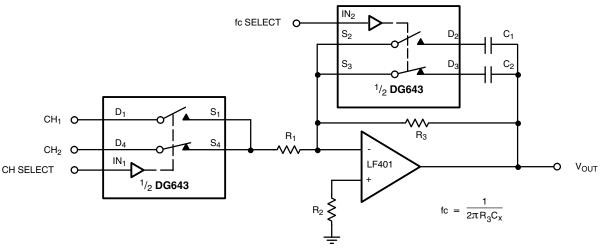


Figure 10. Active Low Pass Filter with Selectable Inputs and Break Frequencies

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?70058.



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	MILLIMETERS		HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050) BSC		
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-0652	ECN: C-06527-Rev. I. 11-Sep-06					

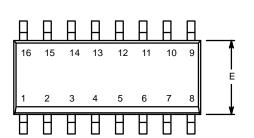
DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06





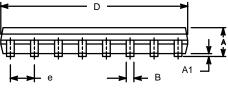
SOIC (NARROW): 16-LEAD JEDEC Part Number: MS-012

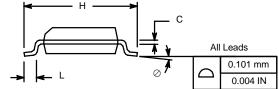


	MILLIMETERS		INC	HES
Dim	Min	Max	Min	Max
Α	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
В	0.38	0.51	0.015	0.020
С	0.18	0.23	0.007	0.009
D	9.80	10.00	0.385	0.393
E	3.80	4.00	0.149	0.157
е	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
L	0.50	0.93	0.020	0.037
0	0°	8°	0°	8°
FCN: S-0	3946—Rev F	09lul-01		

ECN: S-03946—Rev. F, 09-Jul-01

DWG: 5300



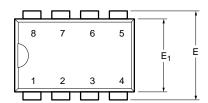


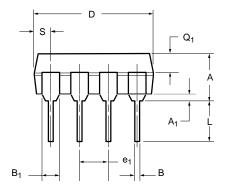
www.vishay.com 02-Jul-01

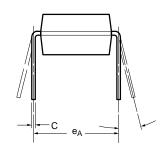




PDIP: 8-LEAD







MILLIMETERS INCHES							
	MILLIM	IETERS	INC	HES			
Dim	Min	Max	Min	Max			
Α	3.81	5.08	0.150	0.200			
A ₁	0.38	1.27	0.015	0.050			
В	0.38	0.51	0.015	0.020			
B ₁	0.89	1.65	0.035	0.065			
С	0.20	0.30	0.008	0.012			
D	9.02	10.92	0.355	0.430			
Е	7.62	8.26	0.300	0.325			
E ₁	5.59	7.11	0.220	0.280			
e ₁	2.29	2.79	0.090	0.110			
e _A	7.37	7.87	0.290	0.310			
L	2.79	3.81	0.110	0.150			
Q_1	1.27	2.03	0.050	0.080			
S	0.76	1.65	0.030	0.065			
ECN: S-0	FCN: S-03946—Rev F 09-Jul-01						

DWG: 5478

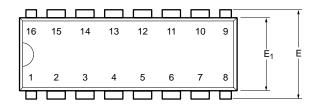
15° MAX

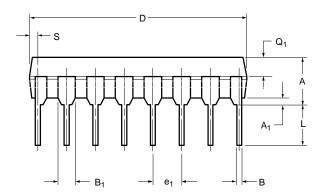
NOTE: End leads may be half leads.

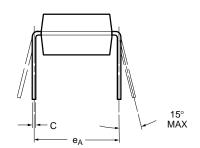
Document Number: 71259 www.vishay.com 05-Jul-01



PDIP: 16-LEAD







	MILLIN	IETERS	INC	HES	
Dim	Min	Max	Min	Max	
Α	3.81	5.08	0.150	0.200	
A ₁	0.38	1.27	0.015	0.050	
В	0.38	0.51	0.015	0.020	
B ₁	0.89	1.65	0.035	0.065	
С	0.20	0.30	0.008	0.012	
D	18.93	21.33	0.745	0.840	
E	7.62	8.26	0.300	0.325	
E ₁	5.59	7.11	0.220	0.280	
e ₁	2.29	2.79	0.090	0.110	
e _A	7.37	7.87	0.290	0.310	
L	2.79	3.81	0.110	0.150	
Q ₁	1.27	2.03	0.050	0.080	
S	0.38	1.52	.015	0.060	
ECN: S-03946—Rev. D, 09-Jul-01					

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RECOMMENDED MINIMUM PADS FOR SO-8



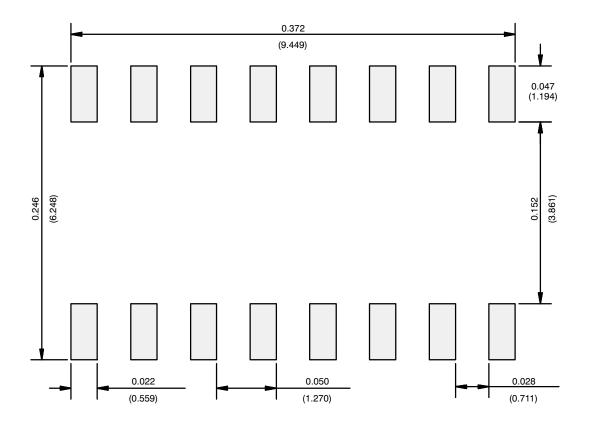
Recommended Minimum Pads Dimensions in Inches/(mm)

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RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

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